Preferred Device

# Self-Protected FET with Temperature and Current Limit

# 42 V, 2.0 A, Single N-Channel, SOT-223

HDPlus<sup>™</sup> devices are an advanced series of power MOSFETs which utilize ON Semiconductors latest MOSFET technology process to achieve the lowest possible on–resistance per silicon area while incorporating smart features. Integrated thermal and current limits work together to provide short circuit protection. The devices feature an integrated Drain–to–Gate Clamp that enables them to withstand high energy in the avalanche mode. The Clamp also provides additional safety margin against unexpected voltage transients. Electrostatic Discharge (ESD) protection is provided by an integrated Gate–to–Source Clamp.

## Features

- Current Limitation
- Thermal Shutdown with Automatic Restart
- Short Circuit Protection
- I<sub>DSS</sub> Specified at Elevated Temperature
- Avalanche Energy Specified
- Slew Rate Control for Low Noise Switching
- Overvoltage Clamped Protection
- Pb–Free Packages are Available

## Applications

- Lighting
- Solenoids
- Small Motors

## **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit	
Drain-to-Source Voltage Internally Clamped	V <sub>DSS</sub>	42	V	
Drain-to-Gate Voltage Internally Clamped ( $R_G = 1.0 M\Omega$ )	V <sub>DGR</sub>	42	V	
Gate-to-Source Voltage	V <sub>GS</sub>	±14	V	
Continuous Drain Current	Ι <sub>D</sub>	Internally Limited		
$ \begin{array}{ll} \mbox{Power Dissipation} & @\ T_A = 25^\circ C \ (Note \ 1) \\ & @\ T_A = 25^\circ C \ (Note \ 2) \\ & @\ T_T = 25^\circ C \ (Note \ 3) \\ \end{array} $	P <sub>D</sub>	1.1 1.7 8.9	W	
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	–55 to 150	°C	
	E <sub>AS</sub>	150	mJ	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



# **ON Semiconductor®**

## http://onsemi.com

V <sub>(BR)DSS</sub> (Clamped)	R <sub>DS(ON)</sub> TYP	I <sub>D</sub> MAX
42 V	165 mΩ @ 10 V	2.0 A*

\*Max current limit value is dependent on input condition.



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## MARKING DIAGRAM



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 1)	R <sub>θJA</sub>	114	°C/W
Junction-to-Ambient - Steady State (Note 2)	R <sub>θJA</sub>	72	
Junction-to-Tab - Steady State (Note 3)	R <sub>θJT</sub>	14	

Surface-mounted onto min pad FR4 PCB, (2 oz. Cu, 0.06" thick).
Surface-mounted onto 2" sq. FR4 board (1" sq., 1 oz. Cu, 0.06" thick).
Surface-mounted onto min pad FR4 PCB, (2 oz. Cu, 0.06" thick).

### ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	(1 - 0) (1 - 10)	$T_J = 25^{\circ}C$	42	46	55	V
(Note 4)		$v_{GS} = 0 v, i_D = 10 mA$	T <sub>J</sub> = 150°C	40	45	55	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V 0.V.V 22.V	T <sub>J</sub> = 25°C		0.25	4.0	μΑ
		$v_{GS} = 0 v, v_{DS} = 32 v$	T <sub>J</sub> = 150°C		1.1	20	
Gate Input Current	I <sub>GSSF</sub>	$V_{DS}$ = 0 V, $V_{GS}$ =	5.0 V		50	100	μΑ

## **ON CHARACTERISTICS** (Note 4)

Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{GS} = V_{DS}$ , $I_D = 150 \ \mu A$		1.3	1.8	2.2	V
Gate Threshold Temperature Coefficient	V <sub>GS(th)</sub> /T <sub>J</sub>				4.0	6.0	−mV/°C
Static Drain-to-Source On-Resistance	R <sub>DS(on)</sub>	$T_J = 25^{\circ}C$			165	200	mΩ
		$v_{GS} = 10 v, I_D = 1.7 A$	T <sub>J</sub> = 150°C		305	400	
		T <sub>J</sub>			195	230	
		$v_{GS} = 5.0 \text{ v}, I_D = 1.7 \text{ A}$	T <sub>J</sub> = 150°C		360	460	
			$T_J = 25^{\circ}C$		190	230	
		$v_{GS} = 5.0 \text{ v}, \text{ I}_{D} = 0.5 \text{ A}$	$T_J = 150^{\circ}C$		350	460	
Source–Drain Forward On Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 7.0 A			1.0		V

#### SWITCHING CHARACTERISTICS

Turn-on Time	t <sub>d(on)</sub>	$V_{GS} = 10 \text{ V}, V_{DD} = 12 \text{ V},$	20	30	μs
Turn-off Time	t <sub>d(off)</sub>	$D = 2.3 \text{ A}, \text{ KL} = 4.7 \text{ s}_2,$ (10% V <sub>in</sub> to 90% I <sub>D</sub> )	65	100	
Slew Rate On	dV <sub>DS</sub> /dt <sub>on</sub>	$R_L$ = 4.7 Ω, $V_{in}$ = 0 to 10 V, $V_{DD}$ = 12 V, 70% to 50%	1.2		V/µs
Slew-Rate Off	dV <sub>DS</sub> /dt <sub>off</sub>	$R_L$ = 4.7 Ω, $V_{in}$ = 0 to 10 V, $V_{DD}$ = 12 V, 50% to 70%	0.5		

#### **SELF PROTECTION CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted) (Note 5)

Current Limit	I <sub>LIM</sub>		T <sub>J</sub> = 25°C	3.1	4.7	6.3	А
		$v_{\rm DS} = 10 v, v_{\rm GS} = 5.0 v$	T <sub>J</sub> = 150°C	2.0	3.2	4.3	
			T <sub>J</sub> = 25°C	3.8	5.7	7.6	
		$v_{\rm DS} = 10 v, v_{\rm GS} = 10 v$	T <sub>J</sub> = 150°C	2.8	4.3	5.7	
Temperature Limit (Turn-off)	T <sub>LIM(off)</sub>	V <sub>GS</sub> = 5.0 V		150	175	200	°C
Temperature Limit (Circuit Reset)	T <sub>LIM(on)</sub>	V <sub>GS</sub> = 5.0 V		135	160	185	
Temperature Limit (Turn–off)	T <sub>LIM(off)</sub>	V <sub>GS</sub> = 10 V		150	165	185	
Temperature Limit (Circuit Reset)	T <sub>LIM(on)</sub>	V <sub>GS</sub> = 10 V		135	150	170	

### ESD ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Electro-Static Discharge Capability	ESD	Human Body Model (HBM)	4000		V
		Machine Model (MM)	400		

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
Fault conditions are viewed as beyond the normal operating range of the part.

## TYPICAL PERFORMANCE CURVES



# **TYPICAL PERFORMANCE CURVES**



Figure 9. Thermal Response

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NIF5002NT1	SOT-223	1000 / Tape & Reel
NIF5002NT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NIF5002NT3	SOT-223	4000 / Tape & Reel
NIF5002NT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

PIN 1. GATE 2. DRAIN

3. SOURCE 4. DRAIN

	м	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.50	1.63	1.75	0.060	0.064	0.068	
A1	0.02	0.06	0.10	0.001	0.002	0.004	
b	0.60	0.75	0.89	0.024	0.030	0.035	
b1	2.90	3.06	3.20	0.115	0.121	0.126	
С	0.24	0.29	0.35	0.009	0.012	0.014	
D	6.30	6.50	6.70	0.249	0.256	0.263	
E	3.30	3.50	3.70	0.130	0.138	0.145	
е	2.20	2.30	2.40	0.087	0.091	0.094	
e1	0.85	0.94	1.05	0.033	0.037	0.041	
L1	1.50	1.75	2.00	0.060	0.069	0.078	
HE	6.70	7.00	7.30	0.264	0.276	0.287	
θ	0°	-	10°	0°	-	10°	
STYLE 3	8:						





\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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